Exploiting the DRAM row hammer bug to gain kernel privileges

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Introduction

Exploit !

... without exploiting software bug

Row hammer repeated accesses DRAM's row DRAM chipset

DRAM Structure

DRAM chipset



DRAM Structure

DRAM chipset



DRAM Structure



ex) 4GB memory = 2ranks * 8 banks *8K per row * 32768 rows

DRAM? Dynamic RAM !

01

DRAM is really dynamic!







DRAM row buffer



DRAM row buffer





- raise wordline to high voltage





- raise wordline to high voltage
- Connecting capacitor to bitline



- raise wordline to high voltage
- Connecting capacitor to bitline _



Æ - Access to row buffer are fast





- raise wordline to high voltage
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- Access to row buffer are fast



- raise wordline to high voltage
- Connecting capacitor to bitline
- DRO (Destructive Read Out)



Row buffer

- Access to row buffer are fast









Cells are capacitor!

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- They leak charge
- Cells should be periodically refreshed
- Refresh circuitry perform refresh cycle within the refresh time interval : 64ms

Introduction to rowhammer problems

02

Introduction to rowhammer problems



This "aggressor" row is repeatedly activated (hammered)







This "aggressor" row is repeatedly activated (hammered)







Bad Cells





- Randomly distributed
- Constantly flip when hammered
- varies by DRAM module
 - % of rows with bad cells : Varies from 30% to 99.9%

Understand bit flipping

by looking hammering code !

03

Challenge 1. Right way to flip bit. 1? 2?



Challenge 1. Right way to flip bit. 1? 2?



Challenge 1. Right way to flip bit. 1? 2?



Challenge 1. Right way to flip bit. 1? 2?



Challenge 1. Right way to flip bit. 1? 2?



Challenge 1. Right way to flip bit. (1)? (2)?





Bit flip code:

1. OPEN – CLOSE rows repeatedly

pick 2 addresses : Same Bank Different Rows (SBDR)

2. CPU cache by clflush






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Exploit a bit flip

Native Client Sandbox
Linux Kernel

04

Exploit a bit flip

Native Client Sandbox
Linux Kernel

04

Native Client Sandbox





- $\checkmark\,$ Sandbox for running C/C++ "native code" on the web
- ✓ Used in chrome
- ✓ Goal : make C/C++ code as safe as javascript
- ✓ In-process sandbox
 - Can't call host OS's syscalls

Native Client Sandbox





- ✓ Sandbox for running C/C++ "native code" on the web
- ✓ Used in chrome



Challenges

- 1. Mark shellcode as executable
- 2. Jump to shellcode

Challenges

- 1. Mark shellcode as executable
- 2. Jump to shellcode



This conceals:

20ea2:	0f (05	syscall						
20ea4:	eb	0c	jmp	//	Jump	to	next	hidden	instr
20ea6:	f4		hlt	//	Padd	ing			

Challenges

- 1. Mark shellcode as executable
- 2. Jump to shellcode

Only allows "jmp *%rax" as part of this safe indirect jump sequence:



Exploit a bit flip

Native Client Sandbox Linux Kernel

04

normal Linux process



Spray most of physical memory with page tables
Bit flip!

Kernel privilege escalation

Linux kernel exploit





Create shared memory



1. mmap() data file repeatedly

2. Spray memory page table



Map it multiple times



1. mmap() data file repeatedly

2. Spray memory page table







Virtual Address Space



Physical Memory



Virtual Address Space

Physical Memory



Got write access to page table!





Experimental results

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	Laptop model	Laptop year	CPU family (microarchitectu re)	DRAM manufacturer	Saw bit flip
1	Model #1	2010	Family V	DRAM vendor E	yes
2	Model #2	2011	Family W	DRAM vendor A	yes
3	Model #2	2011	Family W	DRAM vendor A	yes
4	Model #2	2011	Family W	DRAM vendor E	no
5	Model #3	2011	Family W	DRAM vendor A	yes
6	Model #4	2012	Family W	DRAM vendor A	yes
7	Model #5	2012	Family X	DRAM vendor C	no
8	Model #5	2012	Family X	DRAM vendor C	no
9	Model #5	2013	Family X	DRAM vendor B	yes
10	Model #5	2013	Family X	DRAM vendor B	yes
11	Model #5	2013	Family X	DRAM vendor B	yes
12	Model #5	2013	Family X	DRAM vendor B	yes
13	Model #5	2013	Family X	DRAM vendor B	yes
14	Model #5	2013	Family X	DRAM vendor B	yes
15	Model #5	2013	Family X	DRAM vendor B	yes

	Laptop model	Laptop year	CPU family (microarchitectu re)	DRAM manufacturer	Saw bit flip
16	Model #5	2013	Family X	DRAM vendor B	yes
17	Model #5	2013	Family X	DRAM vendor C	no
18	Model #5	2013	Family X	DRAM vendor C	no
19	Model #5	2013	Family X	DRAM vendor C	no
20	Model #5	2013	Family X	DRAM vendor C	no
21	Model #5	2013	Family X	DRAM vendor C	yes
22	Model #5	2013	Family X	DRAM vendor C	yes
23	Model #6	2013	Family Y	DRAM vendor A	no
24	Model #6	2013	Family Y	DRAM vendor B	no
25	Model #6	2013	Family Y	DRAM vendor B	no
26	Model #6	2013	Family Y	DRAM vendor B	no
27	Model #6	2013	Family Y	DRAM vendor B	no
28	Model #7	2012	Family W	DRAM vendor D	no
29	Model #8	2014	Family Z	DRAM vendor A	no

15/29 Machines were vulnerable...

Rowhammer defenses

 $\mathbf{06}$

Rowhammer detection

• Software binary analysis



Rowhammer detection

• Software binary analysis



Rowhammer neutralization

- *G-CATT
 - ✓ Isolate user space / kernel space in physical memory
 - \checkmark attacker cannot exploit bit flips in kernel memory

* "CAn't Touch This: Software-only Mitigation against Rowhammer Attacks targeting Kernel Memory", F.Brasser et al. (2017.08)

Rowhammer detection

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 - ✓ Isolate user space / kernel space in physical memory
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Rowhammer elimination

- TRR (Target Row Refresh) : Identify frequently accessed DRAM addresses
- tREFI (time of REfresh Interval) 🛶 e.g. Intel Skylake, Kaby lake
- ECC memory (Error Correcting Code)

* "CAn't Touch This: Software-only Mitigation against Rowhammer Attacks targeting Kernel Memory", F.Brasser et al. (2017.08)

"Based on the analysis by Third I/O, we believe that this problem is significantly worse than what is being reported," the paper warned. "And it is still visible on some DDR4 memory modules."

Mark Lanteigne, Third I/O CTO and founder, told Ars there's no immediate danger of Rowhammer being exploited maliciously to hijack the security of computers that use the vulnerable memory chips. Still, he said his assessment presents a significantly



FURTHER READING

Cutting-edge hack gives super user status by exploiting DRAM weakness

less comforting picture than those painted by Samsung, Micron, and other DDR manufacturers. Samsung, he said, has largely declared its DDR4 product line to be "Rowhammer free" because of technology it calls TRR, or targeted row refresh, which makes chips better able to withstand large numbers of malicious accesses that come in rapid succession during the attack. Micron, meanwhile, has also praised the benefits of TRR in its DDR4 products.

✓ Isolate DDR4 and Rowhammer

- Attacke When Rowhammer was first discovered and discussed, Samsung claimed that its DDR4 would not be susceptible to this attack method due to its use of Targeted Row Refresh inside devices. Micron followed suit with a statement that TRR mode is implemented in the background of its hardware as well. Third I/O's testing shows that in Micron's case, at least, this protection is imperfectly implemented. The paper states:
- TRR (Target Row Refresh) : Identify frequently accessed DRAM addresses
- tREFI (time of REfresh Interval) >>> e.g. Intel Skylake, Kaby lake
- ECC memory (Error Correcting Code)

* https://www.extremetech.com/extreme/224860-new-paper-alleges-servers-some-ddr4-dram-still-vulnerable-to-critical-rowhammer-attack ** https://arstechnica.com/information-technology/2016/03/once-thought-safe-ddr4-memory-shown-to-be-vulnerable-to-rowhammer/



Conclusion & Recent study

 $\mathbf{07}$













- Arrange Refresh-only row buffer



- Arrange Refresh-only row buffer



- Arrange Refresh-only row buffer



- Arrange Refresh-only row buffer

Refresh-only row buffer



▲ Ordinary rowhammer







THANK YOU